Features

- Trench Power LV MOSFET Technology
- Moisture Sensitivity Level 1
- Halogen Free. “Green” Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

N-Channel MOSFET

Maximum Ratings

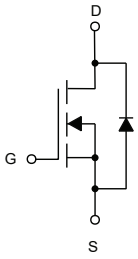
- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 136°C/W Junction to Ambient(Note2)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Volltage		V_{GS}	±20	V
Continuous Drain Current	T_A=25°C	I_D	2.0	A
	T_A=100°C		1.2	
Pulsed Drain Current(Note3)		I_{DM}	8.0	A
Total Power Dissipation(Note4)		P_D	0.92	W

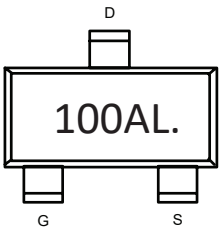
Note:

1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-ambient thermal resistance.

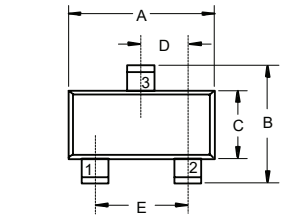
Internal Structure and Marking Code



1. GATE
2. SOURCE
3. DRAIN

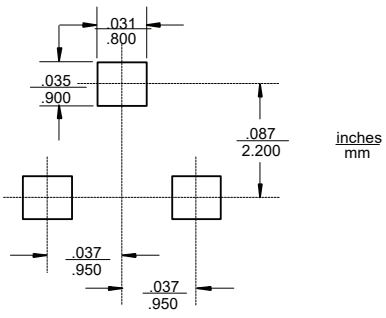


SOT-23-3L



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.113	0.117	2.87	2.97	
B	0.108	0.112	2.75	2.85	
C	0.061	0.065	1.55	1.65	
D	0.036	0.038	0.914	0.965	
E	0.073	0.077	1.85	1.95	
G	0.0016	0.0039	0.04	0.100	
H	0.041	0.045	1.05	1.15	
J	0.006	0.007	0.14	0.17	
K	0.012	0.020	0.30	0.50	

Suggested Solder Pad Layout



Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA	100			V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	1.3	1.8	2.3	V
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V, V_{GS}=0V			1	μA
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=2A		77	100	mΩ
		V_{GS}=4.5V, I_D=1A		84	110	
Gate Resistance	R_g	f=1 MHz, Open Drain		1.7		Ω
Diode Characteristics						
Diode Forward Current	I_S				2.0	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_s=2A			1.2	V
Reverse Recovery Time	t_{rr}	I_F=2A,di/dt=100A/us		22		nS
Reverse Recovery Charge	Q_{rr}			25		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=50V,V_{GS}=0V, f=1MHz		903		pF
Output Capacitance	C_{oss}			30		
Reverse Transfer Capacitance	C_{rss}			28		
Total Gate Charge	Q_g	V_{DS}=50V,V_{GS}=10V,I_D=2A		23.2		nC
Gate-Source Charge	Q_{gs}			2.6		
Gate-Drain Charge	Q_{gd}			6.1		
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=50V,V_{GS}=10V, I_D=2A,R_G =3Ω		7.4		ns
Turn-on Rise Time	t_r			3.4		
Turn-off Delay Time	$t_{d(off)}$			28.6		
Turn-off Fall Time	t_f			4.3		

Curve Characteristics

Fig. 1 - Typical Output Characteristics

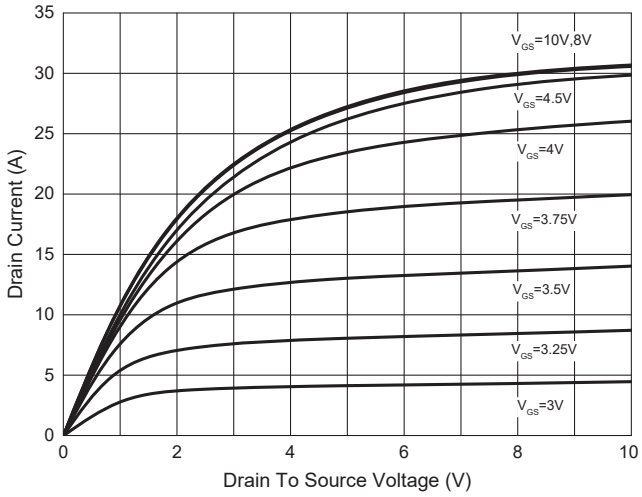


Fig. 2 - Transfer Characteristics

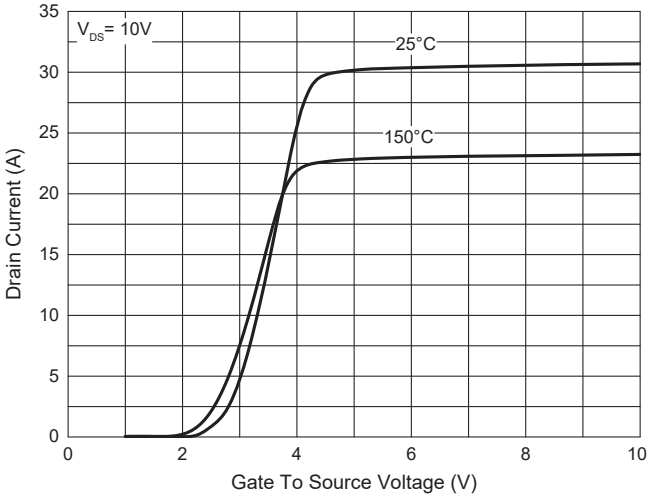


Fig.3-$R_{DS(ON)}$-V_{GS}

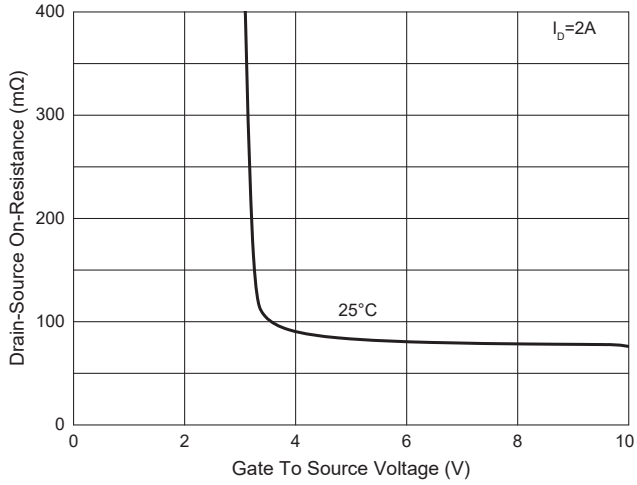


Fig.4-$R_{DS(ON)}$-I_D

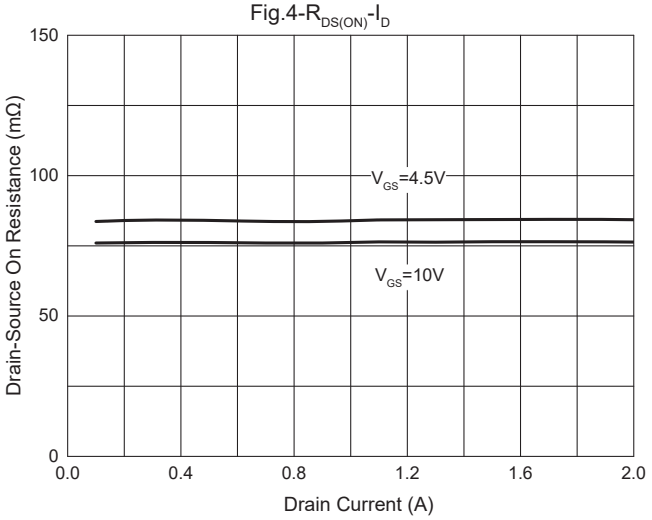


Fig. 5 - Capacitance Characteristics

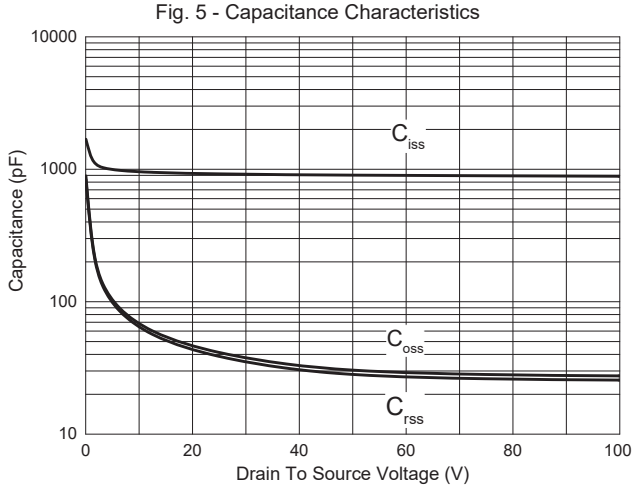
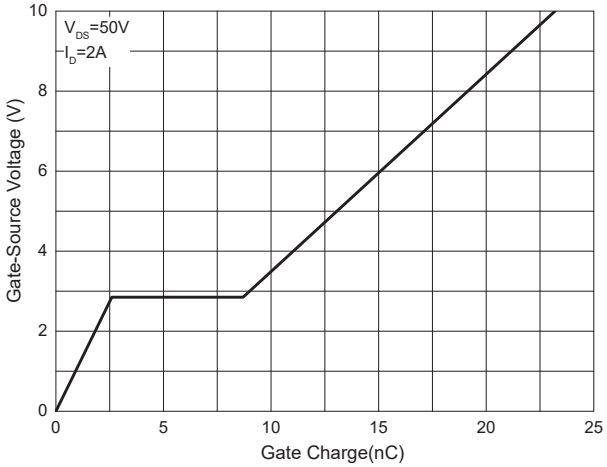


Fig. 6 - Gate Charge



Curve Characteristics

Fig. 7 - Normalized Threshold Voltage

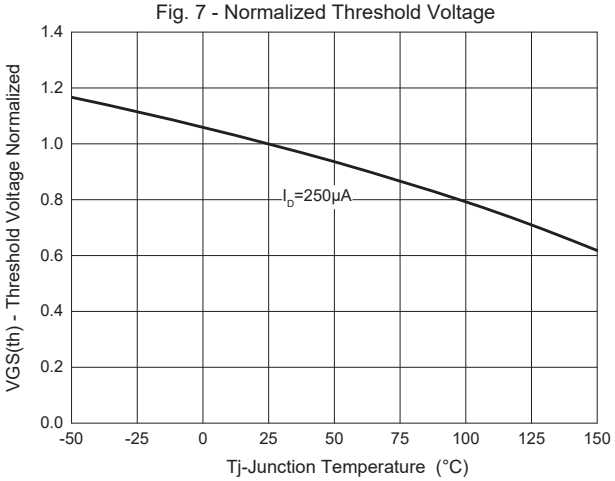


Fig. 8 - Normalized On Resistance Characteristics

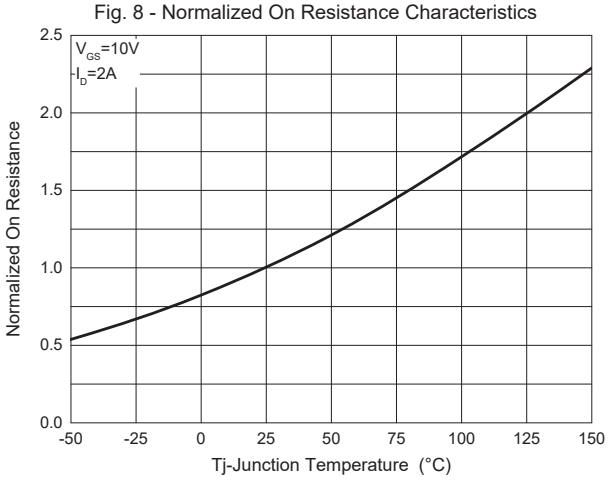


Fig.9-I_S-V_{SD}

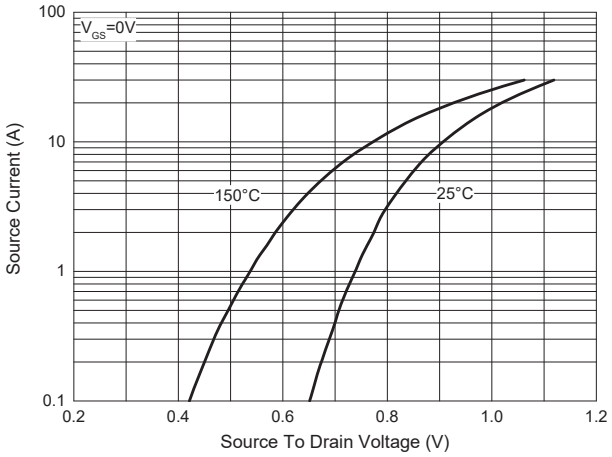


Fig. 10 - Drain Current

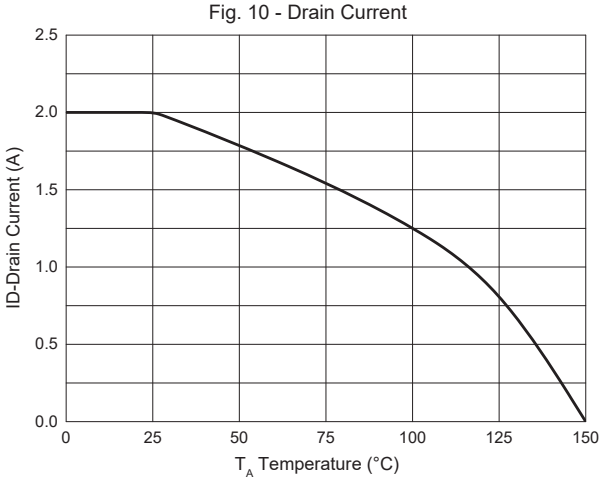
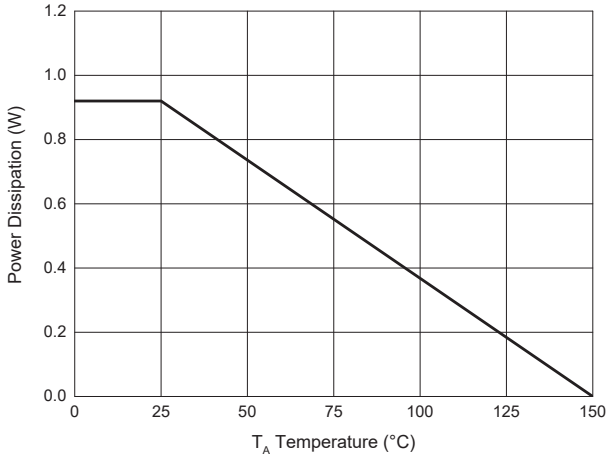


Fig. 11 - PD Dissipation



Curve Characteristics

Fig. 12 - Safe Operation Area

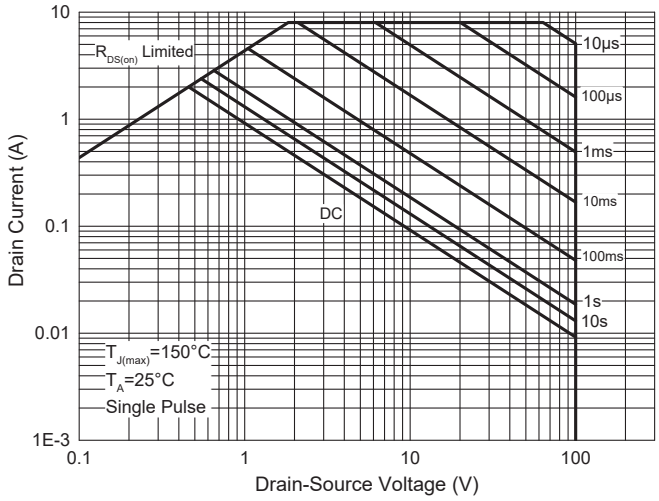
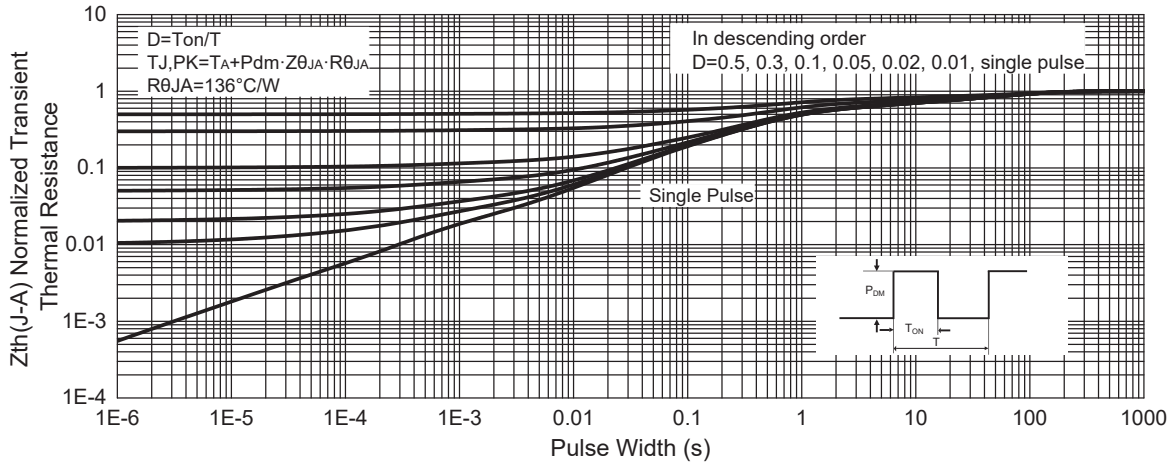


Fig. 13 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel:3Kpcs/Reel